

## **Description**

The SiT9365 is a differential MEMS XO supporting standard frequencies between 25 MHz and 325 MHz, and engineered for low-jitter applications. Utilizing SiTime's unique DualMEMS® temperature sensing and TurboCompensation® technology, the SiT9365 delivers exceptional dynamic performance by providing resistance to airflow, thermal gradients, shock and vibration. This device also integrates multiple on-chip regulators to filter power supply noise, eliminating the need for a dedicated external LDO.

The SiT9365 can be factory programmed for specific combinations of frequency, stability, voltage, and output signaling. Programmability enables designers to optimize clock configurations while eliminating long lead times and customization costs associated with quartz devices where each frequency is custom built.

Standard frequencies and programmability makes this device ideal for telecom, networking, and industrial applications that require a variety of frequencies and operate in noisy environments.

Refer to Manufacturing Notes for proper reflow profile, tape and reel dimension, and other manufacturing related information.

### **Features**

- 32 standard frequencies from 25 MHz to 325 MHz (For additional frequencies, refer to SiT9366 and SiT9367 datasheets)
- LVPECL, Low-swing LVPECL, LVDS and HCSL output signaling
- 0.1 ps RMS phase jitter (random) for Ethernet applications
- Frequency stability as low as ±10 ppm
- Wide temperature ranges from -40°C to 105°C
- Industry-standard packages: 3.2 x 2.5 mm², 7.0 x 5.0 mm² and 5.0 x 3.2 mm² package

## **Applications**

- 10/40/100 Gbps Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers



## **Block Diagram**

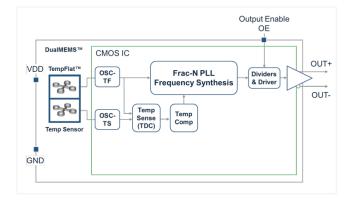


Figure 1. SiT9365 Block Diagram

## **Package Pinout**

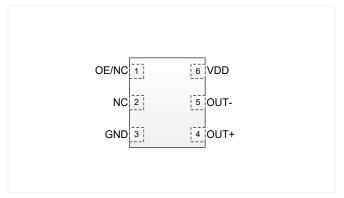
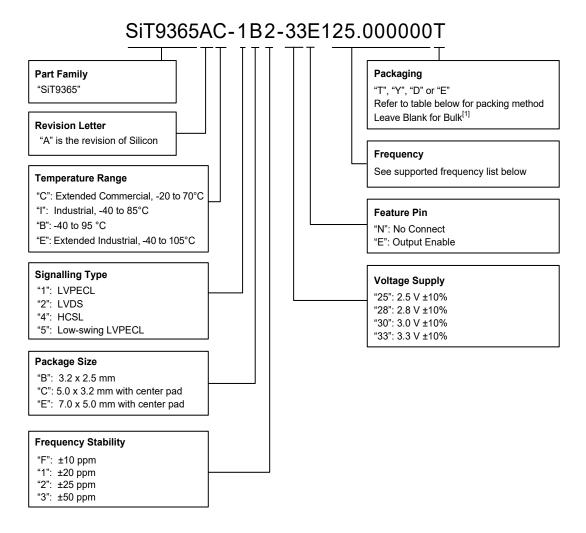


Figure 2. Pin Assignments (Top view) (Refer to Table 7 for Pin Descriptions)



## **Ordering Information**



#### Notes:

1. Bulk is available for sampling only.

### **Table 1. Supported Frequencies**

25.000000 MHz	30.720000 MHz	50.000000 MHz	53.125000 MHz	61.440000 MHz	62.500000 MHz	74.175824 MHz	74.250000 MHz
75.000000 MHz	77.760000 MHz	98.304000 MHz	100.000000 MHz	106.250000 MHz	122.880000 MHz	125.000000 MHz	133.333333 MHz
148.351648 MHz	150.000000 MHz	153.600000 MHz	155.520000 MHz	156.250000 MHz	159.375000 MHz	160.000000 MHz	161.132813 MHz
166.666666 MHz	168.040678 MHz	200.000000 MHz	212.500000 MHz	250.000000 MHz	300.000000 MHz	322.265625 MHz	325.000000 MHz

## Table 2. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	_	_	_	_	Т	Y
5.0 x 3.2			Т	Υ		
3.2 x 2.5	D	E			_	_



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## **Electrical Characteristics**

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination shown in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

Table 3. Electrical Characteristics – Common to LVPECL, Low-swing LVPECL, LVDS and HCSL (All temperature ranges)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			ı	Frequency R	ange	
Output Frequency Range	f		d frequencie and 325.000		MHz	
			F	requency Sta	ability	
Frequency Stability	F_stab	-10	-	+10	ppm	Inclusive of initial tolerance, operating temperature, rated power
		-20	-	+20	ppm	supply voltage and load variations
		-25	-	+25	ppm	
		-50	-	+50	ppm	
First Year Aging	F_1y	-0.7	±0.4	+0.7	ppm	At 85°C
5 Year Aging	F_5y	-1.1	±0.7	+1.1	ppm	At 85°C
10 Year Aging	F_10y	-1.3	±0.8	+1.3	ppm	At 85°C
20 Year Aging	F_20y	-1.5	±1.0	+1.5	ppm	At 85°C
			T	emperature F	Range	
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial
		-40	-	+85	°C	Industrial
		-40	-	+95	°C	
		-40	-	+105	°C	Extended Industrial
				Supply Volt	age	
Supply Voltage	Vdd	2.97	3.30	3.63	V	
		2.70	3.00	3.30	V	
		2.52	2.80	3.08	V	
		2.25	2.50	2.75	V	
			Inj	out Characte	ristics	
Input Voltage High	VIH	70%	-	-	Vdd	Pin 1, OE
Input Voltage Low	VIL	-	-	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	-	100	-	kΩ	Pin 1, OE logic high or logic low
			Out	put Charact	eristics	
Duty Cycle	DC	45	_	55	%	
			Sta	rtup and OE	Timing	
Startup Time	T_start	-	-	3.0	ms	Measured from the time Vdd reaches its rated minimum value.
OE Enable/Disable Time	T_oe	-	-	3.8	μs	f = 156.25 MHz. Measured from the time OE pin reaches rated VIH and VIL to the time clock pins reach 90% of swing and high-Z. See Figure 8 and Figure 9.



Table 4. Electrical Characteristics – LVPECL, Low-swing LVPECL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Cur	rent Consu	mption	
Current Consumption	ldd	-	_	89	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	-	-	58	mA	OE = Low
Output Disable Leakage Current	I_leak	-	0.15	-	μА	OE = Low
Maximum Output Current	I_driver	-	-	30	mA	Maximum average current drawn from OUT+ or OUT-
			Output Ch	aracteristic	s for LVP	PECL
Output High Voltage	VOH	Vdd-1.1	_	Vdd-0.7	٧	See Figure 4
Output Low Voltage	VOL	Vdd-1.9	-	Vdd-1.5	V	See Figure 4
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 5
Rise/Fall Time	Tr, Tf	-	225	290	ps	20% to 80%. See Figure 5
		Outpu	ut Characte	ristics for I	_ow-swin	g LVPECL
Output High Voltage	VOH	Vdd-1.2	-	Vdd-0.75	V	See Figure 4
Output Low Voltage	VOL	Vdd-1.8	-	Vdd-1.25	V	See Figure 4
Output Differential Voltage Swing	V_Swing	0.4	1	1.2	V	Output frequency less than or equal to 220 MHz, See Figure 5
		0.4	1	1.6	V	Output frequency greater than 220 MHz, See Figure 5
Rise/Fall Time	Tr, Tf	-	225	290	ps	20% to 80%. See Figure 5
			Jitter –	7.0 x 5.0 mi	m Packag	je
RMS Period Jitter <sup>[2]</sup>	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	-	0.225	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		_	0.225	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
	•	Jitter -	- 5.0 x 3.2 ı	nm and 3.2	x 2.5 mm	n Packages
RMS Period Jitter <sup>[2]</sup>	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3V or 2.5V
RMS Phase Jitter (random)		-	0.225	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		-	0.225	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.

#### Notes

Measured according to JESD65B.



## Table 5. Electrical Characteristics – LVDS

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Curi	rent Consu	mption	
Current Consumption	ldd	_	_	79	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	-	_	58	mA	OE = Low
Output Disable Leakage Current	I_leak	-	0.15	_	μΑ	OE = Low
			Outp	ut Charact	teristics	
Differential Output Voltage	VOD	300	-	450	mV	See Figure 6
Delta VOD	ΔVOD	_	-	50	mV	See Figure 6
Offset Voltage	VOS	1.125	-	1.375	V	See Figure 6
Delta VOS	ΔVOS	_	-	50	mV	See Figure 6
Rise/Fall Time	Tr, Tf	ı	400	470	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%. See Figure 7
			Jitter –	7.0 x 5.0 m	m Packag	ge
RMS Period Jitter[3]	T_jitt	ı	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	ı	0.215	0.265	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		-	0.215	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
		Jitte	er – 5.0 x 3.:	2 and 3.2 x	2.5 mm F	Packages
RMS Period Jitter <sup>[1]</sup>	T_jitt	-	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	I	0.235	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		ı	0.235	0.320	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd Ievels.

#### Notes

3. Measured according to JESD65B.



Table 6. Electrical Characteristics - HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Curi	rent Consu	mption	
Current Consumption	ldd	ı	_	89	mA	Excluding Load Termination Current, Vdd = 3.3 V or 2.5 V
OE Disable Supply Current	I_OE	ı	_	58	mA	OE = Low
Output Disable Leakage Current	I_leak	ı	0.15	-	μΑ	OE = Low
Maximum Output Current	I_driver	ı	_	35	mA	Maximum average current drawn from OUT+ or OUT-
			Outp	out Charac	teristics	
Output High Voltage	VOH	0.60	_	0.90	V	See Figure 4
Output Low Voltage	VOL	-0.05	_	0.08	V	See Figure 4
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.80	V	See Figure 5
Rise/Fall Time	Tr, Tf	ı	360	465	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%. See Figure 5
			Jitter –	7.0 x 5.0 m	m Packag	ge
RMS Period Jitter <sup>[4]</sup>	T_jitt	I	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	1	0.220	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		-	0.220	0.300	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		-	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.
		Jitte	er – 5.0 x 3.	2 and 3.2 x	2.5 mm F	Packages
RMS Period Jitter <sup>[4]</sup>	T_jitt	ı	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, Vdd = 3.3 V or 2.5 V
RMS Phase Jitter (random)	T_phj	I	0.230	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -20 to 70°C and -40 to 85°C
		I	0.230	0.340	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, includes spurs. Temperature ranges -40 to 95°C and -40 to 105°C
		I	0.1	-	ps	f = 156.25 or 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, includes spurs, all Vdd levels.

4. Measured according to JESD65B.

## **Table 7. Pin Description**

Pin	Мар	Functionality				
1	1 OE/NC Output Enable (OE)  Non Connect (NC)		H <sup>[5]</sup> : specified frequency output L: output is high impedance			
'			H or L or Open: No effect on output frequency or other device functions			
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation			
3	GND	Power	VDD Power Supply Ground			
4	OUT+	Output	Oscillator output			
5	OUT-	Output	Complementary oscillator output			
6 <sub>5</sub>	VDD	Power	Power supply voltage <sup>[6]</sup>			

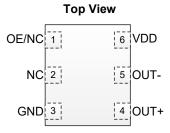


Figure 3. Pin Assignments

- 5. In OE mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven.
  6. A capacitor of value 0.1 μF or higher between VDD and GND is required. An additional 10 μF capacitor between VDD and GND is required for the best phase jitter performance.



### **Table 8. Absolute Maximum Ratings**

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part.

Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Vdd	-0.5	4.0	V
VIH		Vdd + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	°C
Maximum Junction Temperature		130	°C
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	°C

### Table 9. Thermal Considerations[7]

Package	θ <sub>JA</sub> , 4 Layer Board (°C/W)	θ <sub>JC</sub> , Bottom (°C/W)
3225, 6-pin	80	30
5032, 6-pin	53	20
7050, 6-pin	52	19

#### Notes:

### Table 10. Maximum Operating Junction Temperature[8]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C
95°C	120°C
105°C	130°C

#### Notes:

### **Table 11. Environmental Compliance**

Parameter	Test Conditions	Value	Unit	
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	g	
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	g	
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C	
Moisture Sensitivity Level	MSL1 @ 260°C			
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V	
Charge-Device Model ESD Protection	JESD220C101	750	V	
Latch-up Tolerance	JESD7	JESD78 Compliant		

<sup>7.</sup> Refer to JESD51 for  $\theta_{JA}$  and  $\theta_{JC}$  definitions, and reference layout used to determine the  $\theta_{JA}$  and  $\theta_{JC}$  values in the above table.

<sup>8.</sup> Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.



# **Waveform Diagrams**

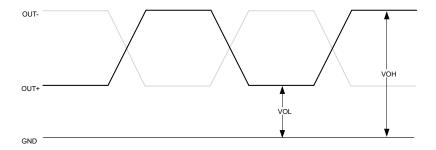


Figure 4. LVPECL, Low-swing LVPECL, and HCSL Voltage Levels per Differential Pin (i.e. OUT+, or OUT-)

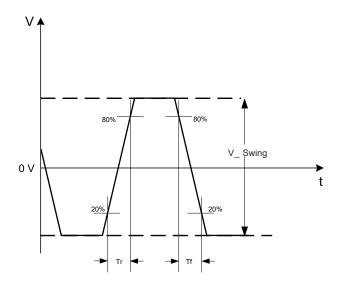


Figure 5. LVPECL, Low-swing LVPECL, and HCSL Voltage Levels Across Differential Pair (i.e. OUT+ minus OUT-)



## **Waveform Diagrams** (continued)

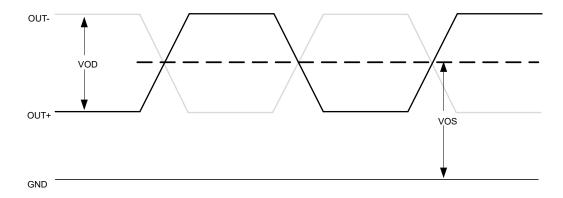


Figure 6. LVDS Voltage Levels per Differential Pin (i.e. OUT+, or OUT-)

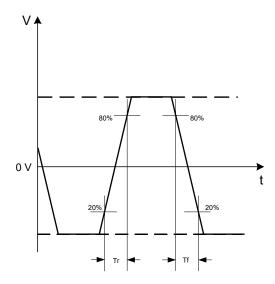


Figure 7. LVDS Differential Waveform (i.e. OUT+ minus OUT-)

## **Timing Diagrams**

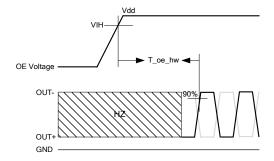


Figure 8. Hardware OE Enable Timing

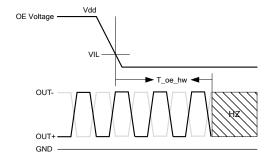


Figure 9. Hardware OE Disable Timing



## **Termination Diagrams**

## LVPECL and Low-swing LVPECL

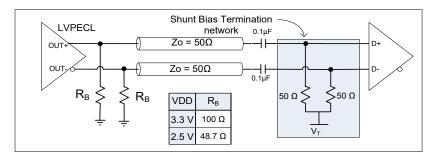


Figure 10. LVPECL and Low-swing LVPECL with AC-coupled Termination

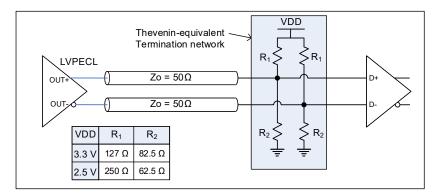


Figure 11. LVPECL and Low-swing LVPECL DC-coupled Load Termination with Thevenin Equivalent Network

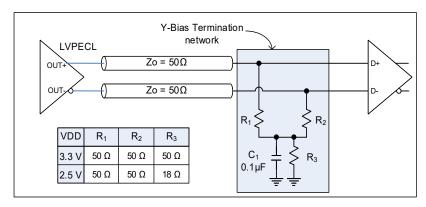


Figure 12. LVPECL and Low-swing LVPECL with Y-Bias Termination

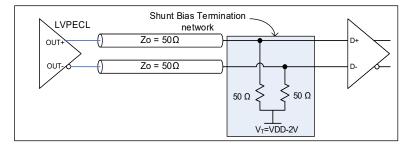


Figure 13. LVPECL and Low-swing LVPECL with DC-coupled Parallel Shunt Load Termination



## **Termination Diagrams** (continued)

## **LVDS**

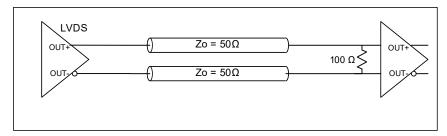


Figure 14. LVDS Single DC Termination at the Load

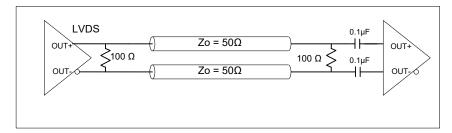


Figure 15. LVDS double AC Termination with Capacitor Close to the Load

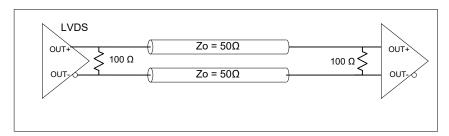


Figure 16. LVDS Double DC Termination

## **HCSL**

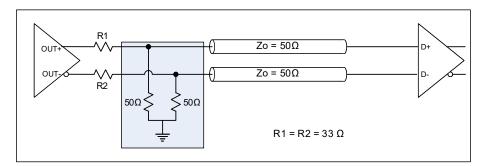
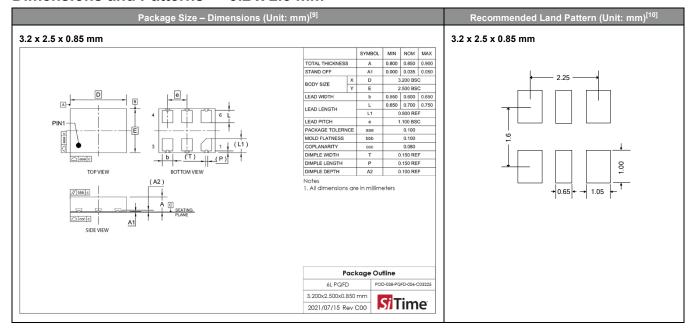


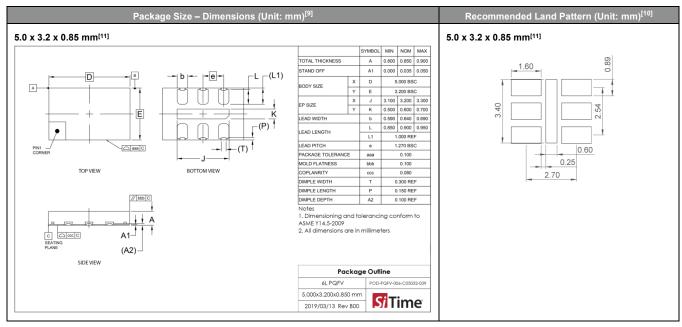
Figure 17. HCSL Interface Termination



## Dimensions and Patterns — 3.2 x 2.5 mm<sup>2</sup>



## Dimensions and Patterns — 5.0 x 3.2 mm<sup>2</sup>

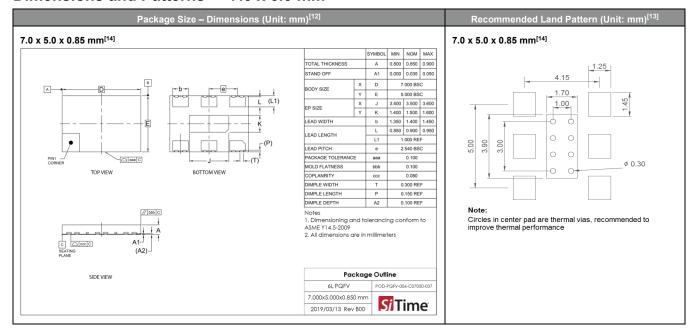


### Notes:

- 9. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 10. A capacitor of value 0.1 μF or higher between VDD and GND is required. An additional 10 μF capacitor between VDD and GND is required for the best phase jitter performance.
- 11. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



## Dimensions and Patterns — 7.0 x 5.0 mm<sup>2</sup>



#### Notes:

- 12. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 13. A capacitor of value 0.1 μF or higher between VDD and GND is required. An additional 10 μF capacitor between VDD and GND is required for the best phase jitter performance.
- 14. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



## **Additional Information**

## **Table 12. Additional Information**

Document	Description	Download Link	
ECCN #: EAR99	Five character designation used on the commerce Control List (CCL) to identify dual use items for export control purposes.	_	
HTS Classification Code: 8542.39.0000	A Harmonized Tariff Schedule (HTS) code developed by the World Customs Organization to classify/define internationally traded goods.		
Part number Generator	Tool used to create the part number based on desired features.	https://www.sitime.com/part-number-generator	
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	https://www.sitime.com/sites/default/files/gated/Manufacturing-Notes-for-SiTime-Products.pdf	
Qualification Reports	RoHS report, reliability reports, composition reports http://www.sitime.com/support/quality-and-reliability		
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies http://www.sitime.com/support/performance-measurement-report		
Termination Techniques	Termination design recommendations http://www.sitime.com/support/application-notes		
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes	
Evaluation Boards	SiT6085/6EB rev. 3.0, SiT6085EB rev.3.1 and SiT6097EB rev. 2.0 Evaluation Boards for Differential Oscillators User Manual	luation Boards for	



## **Revision History**

### **Table 13. Revision History**

Revision	Release Date	Change Summary
1.0	6-Sep-2017	Final release
1.04	17-Apr-2018	Added 5032 package Added -40 to 95°C and -40 to 105°C temperature ranges Corrected minor errors  Added Additional Information Table
1.05	3-Jul-2018	Performed minor edits and updated Ordering Information
1.06	25-Oct-2018	Removed "Contact SiTime" for ±10 ppm
1.07	30-Jul-2019	Updated package Dimensions Drawings Updated Table 9 Thermal Considerations for 5032 package Updated Table 3 specification for First Year Aging Added 5, 10, and 20 year aging specs Added Evaluation Boards SiT6085EB reference in Table 12 Rearranged layout, added Description, Block Diagram and TOC Tightened LVDS minimum VOD specification Added HTS code Added low-swing LVPECL package code and specifications
1.08	17-Aug-2019	Formatting changes
1.09	9-Mar-2021	Updated L1 and Dimple Width package dimensions for 3.2 x 2.5 mm package Updated trademarks, hyperlinks and changed rev table date format
1.1	20-Jul-2021	Updated pin direction in package dimensions for 3.2 x 2.5 mm package

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